

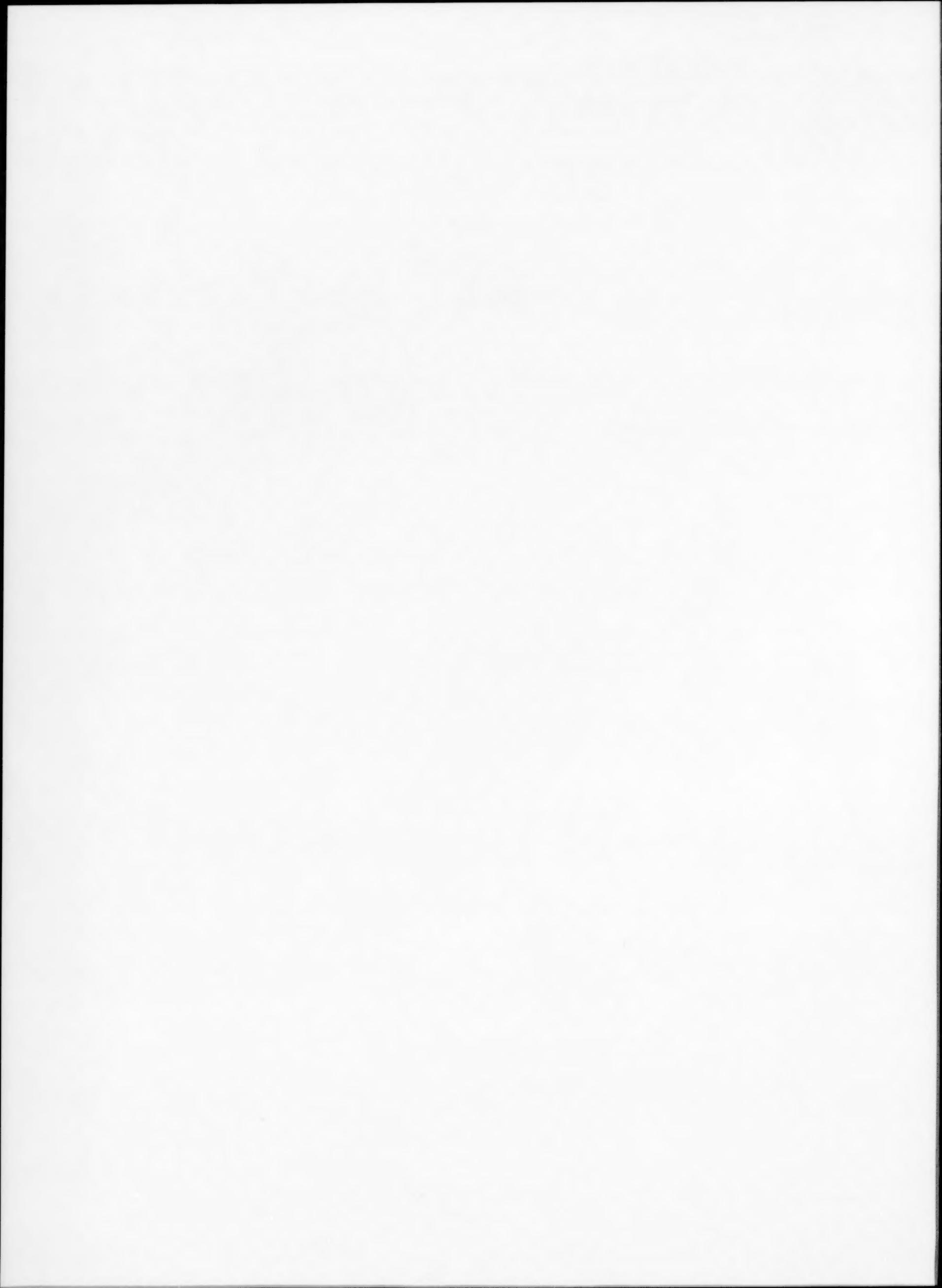


Author Index of Volume 35

- Alves, E.S. 149
Andreev, A. 429
Aoyagi, Y. 364, 467
Arifin, P. 330
Aubrey, J.E. 263
Aulombard, R. 184
Bachmann, K.J. 472
Baeta Moreira, M.V. 149, 391
Baklanov, M.R. 322
Bakueva, L.G. 120
Basmaji, P. 180, 318, 322
Bass, J.M. 489
Beliaev, D. 250, 267
Beton, P.H. 192
Billen, K. 376
Bimberg, D. 295
Bird, J.P. 364
Bi, W.G. 166
Blanter, Y. 429
Briot, O. 184
Brugger, H. 208
Bryant, A.L. 353
Buot, F.A. 303, 51
Burke, T.M. 203
Burroughes, J.H. 198, 203
Button, C.C. 12
Carlone, C. 160
Carvalho, A.T.G. 149
Ceschin, A.M. 401
Chen, M.S. 29
Chen, S. 133
Chen, Y.H. 12
Chi, G.-C. 56
Chin, V.W.L. 176
Chitta, V.A. 318
Choi, J.S. 440
Choi, Y.W. 24, 64
Christen, J. 295
Chua, S.J. 17, 463
Chua, S.-J. 87
Chu, H.Y. 446
Chung, M.S. 440
Clark, A. 176
Courtois, B. 219
Cui, H.L. 256
da Silva, S.W. 180
de Oliveira, A.G. 149, 391
David, J.P.R. 12, 42
Deschler, M. 102
Dewdney, A.J. 345
Diaz, I.F.L. 396
Diaz, J. 34
Dietz, N. 472
Downes, J.R. 357
Du, Q. 382
Eaves, L. 192
Egan, R.J. 176
Eliashevich, I. 34
Elliott, M. 145, 353
Enderlein, R. 250, 267, 396, 401
Erdtmann, M. 34
Evans, R.J. 203
Ezumi, H. 117
Faux, D.A. 357
Fedorovich, A.E. 47
Ferry, D.K. 364
Fontius, U. 245
Forchel, A. 208, 273
Foster, T.J. 192
Fromhold, T.M. 239
Galzerani, J.C. 180
Gavartin, J.L. 459
Gil, B. 184
Göbel, R. 59
Goldys, E.M. 330
Golovin, V.G. 76
Gonçalves, J.L. 401
Gorbach, T.Y. 224
Goto, T. 410
Grey, R. 42
Grimshaw, M.P. 198, 203
Grundmann, M. 295
Guimarães, F.E.G. 318
Gurary, A.I. 97
Gurevich, S.A. 47
Gusev, G.M. 322
Hackbarth, Th. 208
Han, Z.Y. 449
Hayden, R.K. 80
Henini, M. 192, 376
Hill, G. 376
Hiramatsu, M. 68
Hogg, R.A. 42
Hopkinson, M. 12
Horing, N.J.M. 256
Houdayer, A. 160
Houng, M.P. 435
Huang, H.K. 295
Huang, K.C. 259
Hübner, B. 273
Hutchinson, S.V. 376
Hwang, S.-M. 214
Ikeda, Y. 421
Il'in, V.I. 120
Inoue, K. 295
Ishibashi, K. 364
Jackson, M.D. 489
Janning, H. 59
Jin, C.S. 72
Johnson, M.B. 485
Jorio, A. 160
Juang, C. 56
Juergensen, H. 102
Kang, J.-M. 214
Karam, J.M. 219
Karunasiri, G. 463
Keitoku, S. 117
Kelly, M.J. 1, 376
Ke, M. 145
Ke, M.-I. 349
Kestle, A. 145
Kharas, D. 299
Kim, K. 24, 64
Kim, M.-S. 214
Kim, S. 34
Kim, S.-I. 214
Kim, Y. 214
Kobayashi, T. 117
Kochnev, I.V. 47
Koenraad, P.M. 485
Komin, V.V. 47
Komuro, S. 467
Kroll, W.J. 97
Kumar, K. 17
Kuramochi, E. 7
Kuramoto, K. 479
Kwon, O.K. 24, 64
Laiho, R. 372
Laureto, E. 401
Leadbeater, M.L. 198
Lee, E.H. 446
Lee, E.-H. 24, 325, 64
Lee, H.G. 325
Lee, H.J. 230, 234
Lee, J.I. 325
Lee, K.-S. 325, 440
Leite, J.R. 250, 267, 396, 401

- Lei, X.L. 256
 Leong, Y.C. 230
 Levine, A. 401
 Li, C. 372
 Limmer, W. 245
 Lippens, D. 90
 Liu, J. 372
 Liu, M.H. 435
 Liu, S. 133
 Li, Y. 133
 Lozovik, Y. 429
 Lubyshev, D. 318
 Lubyshev, D.I. 180, 322
 Maehashi, K. 295
 Main, P.C. 192
 Marahovka, I.I. 180
 Matsushima, Y. 68
 Matthai, C.C. 349, 459, 489
 Mei, X.B. 166
 Miao, Y.B. 109
 Milekhin, A.G. 180
 Milne, W.I. 138
 Mil'shtein, S. 299
 Min, S.-K. 214
 Miyajima, S. 138
 Mizuno, Y. 156
 Mori, N. 192
 Moy, K. 97
 Muessig, H. 208
 Murray, R. 125, 129, 345
 Musikiin, S.F. 120
 Nabetani, Y. 454
 Na, H.-K. 325
 Nakashima, H. 295
 Nastaushev, Y.V. 322
 Nawaz, R. 353
 Nesterov, S.I. 47
 Nishiya, T. 7
 Noda, S. 406
 Nomura, S. 467
 Nomura, Y. 479
 Nötzel, R. 7
 Nozue, Y. 410
 Ochiai, Y. 364
 Ohmori, K. 68
 Oliveira, J.B.B. 401
 Omling, P. 382
 Orth, A. 208
 O'Reilly, E.P. 357
 Osotchan, T. 176
 Pabla, A.S. 42
 Panzlaff, K. 245
 Parenteau, M. 160
 Paret, J.M. 219
 Park, J.M. 440
 Park, J.S. 463
 Park, P.W. 446
 Park, Y.-K. 214
 Pease, R.F.W. 188
 Peng, Y. 133
 Pepper, M. 198, 203
 Peressi, M. 386
 Prasad, K. 230, 234
 Preobrazhenskii, V.V. 180
 Pusep, Y.A. 180
 Py, M.A. 391
 Quierin, M.A. 198
 Quivy, A.A. 250, 401
 Rabizo, O.V. 120
 Radhakrishnan, K. 109, 230, 234, 449
 Rajagopal, A.K. 303, 51
 Ramrakhiani, M. 493
 Ramvall, P. 382
 Razeghi, M. 34
 Rees, G.J. 42
 Reithmaier, J.P. 208
 Richardson, B. 349
 Ritchie, D.A. 198, 203
 Roberts, C. 129, 345
 Roberts, J.S. 12
 Robson, P.N. 12, 42
 Rodrigues, S.C.P. 250
 Rodriguez-Gironés, P.J. 42
 Rossi, J.C. 322
 Rossow, U. 472
 Rowell, N.L. 160
 Rykov, S.A. 120
 Safonov, A.N. 000
 Saito, M. 267
 Sakaki, H. 284
 Salagaj, T. 97
 Salemink, H.W.M. 485
 Sale, T.E. 12, 42
 Sasaki, A. 278, 406, 454, 479
 Sato, K. 295
 Sato, S. 171
 Sato, Y. 171
 Sauer, R. 245
 Schmitz, D. 102
 Schoenfeld, O. 467
 Schulte, F. 102
 Schumaker, N.E. 97
 Scolfaro, L.M.R. 250, 267, 396
 Scopina, V.I. 47
 Semyagin, B.R. 180
 Sheard, F.W. 239
 Sheng, H. 87
 Shiba, K. 295
 Silva, M.d.P.A. 322
 Sipahi, G.M. 396
 Sizov, F.F. 76
 Skolnick, M.S. 42
 Soares, J.A.N.T. 267
 Solov'ev, S.A. 47
 Song, A. 367
 Song, C.-D. 325
 Stall, R.A. 97
 Steinhagen, F. 59
 Sugano, T. 364, 467
 Sugo, M. 7
 Sun, H. 133
 Su, Y.K. 259
 Svechnikov, G. 224
 Svechnikov, S.V. 76
 Swaminathan, S. 109
 Tabata, A. 401
 Takeuchi, M. 295
 Tamamura, T. 7
 Tang, Z.K. 410
 Tan, H.S. 138, 230, 234
 Taniguchi, K. 421
 Tansley, T.L. 176, 330
 Temmyo, J. 7
 Tetyorkin, V.V. 76
 Thompson, A.G. 97
 Thonke, K. 245
 Thornber, K.K. 256
 Thornton, J.M.C. 489
 Ting, S.K. 230
 Tiong-Palisoc, S. 68
 Tit, N. 386
 Tse, M.S. 230, 234
 Tsuji, K. 421
 Tucker, C.R. 263
 Tu, C.W. 166
 Uekusa, S.-i. 156
 Ullrich, B. 117
 Uno, K. 406
 Usher, B.F. 176
 Usui, A. 288
 Vanbésien, O. 90
 Vaya, P. 17
 Vleuten, W.C.v.d. 485
 Voves, J. 417
 Wakahara, A. 454, 479
 Walker, R. 97
 Wang, J. 192
 Wang, K.L. 463
 Wang, L.J. 34
 Wang, R.L. 259
 Wang, X. 372
 Wang, Y.H. 29, 435
 Weber, S. 245
 Weightman, P. 489
 Weng, J. 230, 234
 Westwood, D.I. 145, 263, 349, 353
 Wilkinson, C.D.W. 263
 Wilkinson, P.B. 239
 Wilks, S.P. 145, 353
 Williams, J.P. 263
 Williams, R.H. 145
 Wolter, J.H. 485
 Woodhead, J. 12, 42
 Woods, R.C. 80
 Wu, D. 34
 Xiaohong, T. 72
 Xu, H. 382
 Xu, W. 334, 341
 Yamaguchi, A.A. 288
 Yamamoto, H. 421
 Yamamoto, K. 364
 Yan, C.H. 166
 Yang, C.C. 259

- Yang, X. 372
Yarn, K.F. 29
Yi, H.-J. 34
Yoon, S.F. 109, 138, 230, 234, 449
Yoshino, K. 68
Yuan, C. 97
- Yu, H. 125, 129, 345
Yu, Q. 372
Zahabi, S.M. 263
Zakheim, D.A. 47
Zawadzki, P. 97
- Zengerle, R. 273
Zhang, D.H. 449
Zhang, X. 184
Zhao, X. 467
Zheng, H. 367, 372
Zhou, X. 230, 234





Subject Index of Volume 35

- Aluminium arsenide**
photoluminescence properties of AlAs/GaAs disordered superlattices with fixed GaAs or AlAs layer thickness 406
- Asymmetric double quantum well**
field dependent vertical-transport studies in $\text{Al}_{0.24}\text{Ga}_{0.76}\text{As}/\text{GaAs}$ double-quantum-well structures 245
- (111)B**
photoluminescence of piezoelectric strained InGaAs–GaAs multi-quantum well p-i-n structures 42
- Band structure calculations**
single heterojunction structures for acoustic charge transfer devices 80
- Blue shifts**
blue shifts from doubly δ -doped heterostructures 345
- Bulk micromachining**
collective fabrication of microsystems compatible with CMOS through the CMP service 219
- Buried layer**
influence of strain relaxation on the electronic properties of buried quantum wells and wires 357
- Cadmium selenide**
zinc doped polycrystalline CdSe films for solar energy conversion 493
- Cadmium sulphide**
luminescence properties of p-type thin CdS films prepared by laser ablation 117
- Cadmium telluride**
vertical electron transport in semiconductor superlattices Monte Carlo simulation 417
- Carbon**
photo-enhanced chemical vapour deposition of hydrogenated amorphous silicon carbon using an internal discharge lamp 138
- Carrier scattering**
low-dimensional transports in GaAs/AlGaAs quasi-one-dimensional wires by a correlation field analysis of the phase coherent interferences 364
- CAD tools for microsystems**
collective fabrication of microsystems compatible with CMOS through the CMP service 219
- Chemical vapour deposition**
analysis of reaction gases flow in CVD processes 156
photo-enhanced chemical vapour deposition of hydrogenated amorphous silicon carbon using an internal discharge lamp 138
- Clusters**
the electronic structure and luminescence properties of porous silicon and silicon nanoclusters 459
- Conductance**
shape effects of the conductance of a quantum ballistic constriction in a two-dimensional electron gas 440
- Conductance fluctuations**
low-dimensional transports in GaAs/AlGaAs quasi-one-dimensional wires by a correlation field analysis of the phase coherent interferences 364
- Conductivity**
electrical conductivity of δ doping superlattices parallel to the growth direction 250
- Confining effect**
theoretical study of resonant tunneling in symmetrical rectangular triple-barrier structures with deep wells 421
- Contact resistance**
characterization of Ni/Ge/Au/Ni/Au contact metallization on AlGaAs/InGaAs heterostructures for pseudomorphic heterojunction field effect transistor application 234
- Correlation field analysis**
low-dimensional transports in GaAs/AlGaAs quasi-one-dimensional wires by a correlation field analysis of the phase coherent interferences 364
- Coupling effects**
investigation of resonant interband tunneling structures using a three-band $\vec{k} \cdot \vec{p}$ model 435
- δ doping**
comparative studies of photoluminescence from n and p δ doping wells in GaAs 396
- Defects**
luminescence centres containing two, three and four hydrogen atoms in radiation-damaged silicon 000
- Delta doping**
blue shifts from doubly δ -doped heterostructures 345
- Deposition rate**
analysis of reaction gases flow in CVD processes 156
- 2DEG**
anomalous peaks in the Shubnikov-de Haas spectra of a top gated AlGaAs/GaAs heterostructure 382
- Diffraction**
growth and characterization of strain-compensated InAsP/GaInP and InGaAs/GaInP multiple quantum wells 166
- Diffusion**
direct optical analysis of the carrier diffusion in semiconductor wire structures 273
- Doping effects**
doping dependence of intersubband transitions in $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ multiple quantum wells 463
luminescence properties of p-type thin CdS films prepared by laser ablation 117
the study of GaAs/InGaAs δ -doping resonant interband tunneling diode 259
- Double barrier quantum well structure**
modulation characteristics of AlAs/GaAs double barrier quantum well resonant tunneling structure at microwave frequencies 446

- Electron conduction**
- anomalous peaks in the Shubnikov-de Haas spectra of a top gated AlGaAs/GaAs heterostructure 382
 - non-linear generation of alternating current harmonics in quantum dot superlattice miniband transport 256
 - shape effects of the conductance of a quantum ballistic constriction in a two-dimensional electron gas 440
- Electronic properties**
- influence of strain relaxation on the electronic properties of buried quantum wells and wires 357
- Electron microscopy**
- ballistic electron emission microscopy of InAs/Ga_{1-x}Al_xAs relaxed heterostructure interfaces 349
 - measurements of interface potentials in quantum wells 299
- Electron-phonon interaction**
- raman scattering in PbI₂ clusters incorporated into zeolite cages 410
- Electron states**
- dual-branch electron waveguide couplers 90
 - self-consistent calculation of electronic states in asymmetric double barrier structure 367
- Electron transport**
- vertical electron transport in semiconductor superlattices Monte Carlo simulation 417
- Electron tunnelling**
- examination of internally delta-doped gallium arsenide resonant tunnelling structures 353
- Elementary excitations**
- the electronic structure and luminescence properties of porous silicon and silicon nanoclusters 459
- Engineered molecular layer epitaxy**
- real-time monitoring of heteroepitaxial growth processes on the silicon(001) surface by p-polarized reflectance spectroscopy 472
- Epitaxial growth**
- novel high temperature metal organic chemical vapor deposition vertical rotating-disk reactor with multizone heating for GaN and related materials 97
- Epitaxial regrowth**
- a closed UHV focused ion beam patterning and MBE regrowth technique 208
- Epitaxial silicon**
- doping dependence of intersubband transitions in Si_{1-x}Ge_x/Si multiple quantum wells 463
- Epitaxy of thin films**
- state-of-the-art control of growth of superlattices and quantum wells 102
- Etching**
- reactive ion etched quantum wire structures for laser applications 47
 - selective wet etching of a GaAs/Al_xGa_{1-x}As heterostructure with citric acid-hydrogen peroxide solutions for pseudomorphic GaAs/Al_xGa_{1-y}As heterofunction field effect transistor fabrication 230
- Excitation spectra**
- excitation spectra of two-dimensional bounded electronic systems in a strong magnetic field 429
- Exciton migration**
- the influence of exciton migration on photoluminescence lifetime in growth-interrupted GaAs/AlAs single quantum wells 125
- Extions**
- thermalization effects of low dimensional excitons in quantum wires and quantum wells 284
- Fabry-Perot cavity**
- noise characteristics of electro-absorptive logic device utilizing asymmetric Fabry-Perot etalon structure in high optical power 64
- Fermi-edge singularity**
- fermi-edge singularity of two dimensional electrons in asymmetric coupled double quantum wells 325
- Fibonacci superlattice**
- quantum-size layered PbS/C structures deposited by pulsed laser evaporation in vacuum 120
- Field profiles**
- measurements of interface potentials in quantum wells 299
- Focused ion beam**
- a closed UHV focused ion beam patterning and MBE regrowth technique 208
- GaAs**
- blue shifts from doubly δ-doped heterostructures 345
 - quantum interference effect in GaAs/AlGaAs double quantum wells 372
- GaAs/AlAs**
- the influence of exciton migration on photoluminescence lifetime in growth-interrupted GaAs/AlAs single quantum wells 125
- GaAs/AlGaAs**
- switching characteristics of nonbiased optical bistability in asymmetric Fabry-Perot S-SEEDs made of extremely shallow quantum well structures 24
- Gallium arsenide**
- a comparison of observed and simulated scanning tunneling images of the reconstructed GaAs(001) surface 489
 - a hole facet wire formed by MBE regrowth over an ex-situ patterned GaAs substrate 203
 - a novel approach in fabrication and study of laterally quantum-confined resonant tunnelling diodes 192
 - Be delta-doped layers in GaAs studied by scanning tunnelling microscopy 485
 - characterization of Ni/Ge/Au/Ni/Au contact metallization on AlGaAs/InGaAs heterostructures for pseudomorphic heterojunction field effect transistor application 234
 - comparative studies of photoluminescence from n and p δ doping wells in GaAs 396
 - critical layer thickness in MOCVD grown InGaAs-GaAs strained quantum wells 184
 - electrical conductivity of δ doping superlattices parallel to the growth direction 250
 - electron mobility in low temperature grown gallium arsenide 330
 - examination of internally delta-doped gallium arsenide resonant tunnelling structures 353
 - fermi-edge singularity of two dimensional electrons in asymmetric coupled double quantum wells 325
 - formation of AlGaAs quantum wires on vicinal GaAs(110) surfaces misoriented 3° toward (111)A by molecular beam epitaxy 295
 - influence of surface structure on surface segregation and alloy properties in (100)- and (311)-oriented InGaAs/GaAs heterostructures 318
 - investigation of the photoluminescence linewidth broadening in symmetric and asymmetric InGaAs/GaAs n-type δ-doped quantum wells 401
 - magnetotunnelling transport phenomena and quantum chaos in semiconductor heterostructures 239
 - native defects in gallium arsenide grown by molecular beam epitaxy and metallorganic chemical vapour deposition: effects of irradiation 160
 - new hole negative differential resistance strained-layer device 87
 - non-linear generation of alternating current harmonics in quantum dot superlattice miniband transport 256
 - photoluminescence in degenerate p-type GaAs layers grown by molecular beam epitaxy 449

- photoluminescence properties of AlAs/GaAs disordered superlattices with fixed GaAs or AlAs layer thickness 406
- photoreflectance investigations of semiconductor device structures 267
- proton implantation of $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ resonant-tunnelling diode structures 376
- role of the InAs monomolecular plane inserted in bulk GaAs 386
- selective wet etching of a $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ heterostructure with citric acid-hydrogen peroxide solutions for pseudomorphic $\text{GaAs}/\text{Al}_x\text{Ga}_{1-y}\text{As}$ heterofunction field effect transistor fabrication 230
- self-organized InGaAs quantum disk lasers 7
- the control and modification of metal-semiconductor interfaces using multi quantum barriers 145
- the study of $\text{GaAs}/\text{InGaAs}$ δ -doping resonant interband tunnelling diode 259
- thermalization effects of low dimensional excitons in quantum wires and quantum wells 284
- top sawtooth grating for $\text{GaAs}/\text{AlGaAs}$ quantum well IR detectors 56
- Gallium indium phosphide**
- visible vertical cavity surface emitting lasers at $\lambda < 650 \text{ nm}$ 12
- Gallium-indium phosphide on silicon(001)**
- real-time monitoring of heteroepitaxial growth processes on the silicon(001) surface by p-polarized reflectance spectroscopy 472
- Gallium nitride**
- novel high temperature metal organic chemical vapor deposition vertical rotating-disk reactor with multizone heating for GaN and related materials 97
- Heterojunctions**
- single heterojunction structures for acoustic charge transfer devices 80
- Heteromaterials**
- growth of $\text{GaAs}-\text{InP}$ heteromaterials and corresponding strain determination 133
- Heterostructures**
- anomalous peaks in the Shubnikov-de Haas spectra of a top gated $\text{AlGaAs}/\text{GaAs}$ heterostructure 382
 - a novel approach in fabrication and study of laterally quantum-confined resonant tunnelling diodes 192
 - ballistic electron emission microscopy of $\text{InAs}/\text{Ga}_{1-x}\text{Al}_x\text{As}$ relaxed heterostructure interfaces 349
 - characterization of $\text{Ni}/\text{Ge}/\text{Au}/\text{Ni}/\text{Au}$ contact metallization on $\text{AlGaAs}/\text{InGaAs}$ heterostructures for pseudomorphic heterojunction field effect transistor application 234
 - charge capture in $\text{AlGaAs}/\text{GaAs}$ heterostructures with disordered antidot lattice 322
 - determination of barrier heights in heterostructures utilising real-space transfer of hot electrons 263
 - electrical conductivity of δ doping superlattices parallel to the growth direction 250
 - influence of surface structure on surface segregation and alloy properties in (100)- and (311)-oriented $\text{InGaAs}/\text{GaAs}$ heterostructures 318
 - magnetotunnelling transport phenomena and quantum chaos in semiconductor heterostructures 239
 - migration of silicon atoms in planar-doped $\text{GaAs}/\text{AlGaAs}$ modulation doped fluid effect transistor heterostructures grown by molecular beam epitaxy 149
 - photo-Hall studies of modulation-doped field-effect transistor heterostructures using $(\text{InAs})_m(\text{GaAs})_n$ superlattice channels 391
 - selective wet etching of a $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ heterostructure with citric acid-hydrogen peroxide solutions for pseudomorphic $\text{GaAs}/\text{Al}_x\text{Ga}_{1-y}\text{As}$ heterofunction field effect transistor fabrication 230
- HEMT**
- photoreflectance investigations of semiconductor device structures 267
- High-field effects**
- non-linear generation of alternating current harmonics in quantum dot superlattice miniband transport 256
- Indium**
- influence of surface structure on surface segregation and alloy properties in (100)- and (311)-oriented $\text{InGaAs}/\text{GaAs}$ heterostructures 318
- Indium aluminum arsenide**
- optical and structural characterizations for optimized growth of $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ on InP substrates by molecular beam epitaxy 109
- Indium arsenide**
- new hole negative differential resistance strained-layer device 87
 - role of the InAs monomolecular plane inserted in bulk GaAs 386
- Indium nitride**
- InN thin-film growth using an ECR plasma source 171
- Indium phosphide**
- hydride — VPE embedding of InAlGaAs laser structures with SI InP:Fe 59
- Infrared detector**
- MBE and MOCVD growth of $\text{AlGaAs}-\text{AlAs}-\text{GaAs}$ double barrier multiple quantum well infrared detector 176
- Infrared photodetectors**
- top sawtooth grating for $\text{GaAs}/\text{AlGaAs}$ quantum well IR detectors 56
- Infrared spectroscopy**
- doping dependence of intersubband transitions in $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ multiple quantum wells 463
- InGaAs**
- the effects of In segregation on the emission properties of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum wells 129
- Intraband relaxation**
- optimized design parameters of $\text{InGaAs}-\text{InP}$ quantum well lasers 17
- Intrinsic defects**
- native defects in gallium arsenide grown by molecular beam epitaxy and metallorganic chemical vapour deposition: effects of irradiation 160
- Ion implantation**
- proton implantation of $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ resonant-tunnelling diode structures 376
- Kinetics of heteroepitaxy**
- real-time monitoring of heteroepitaxial growth processes on the silicon(001) surface by p-polarized reflectance spectroscopy 472
- Laser**
- state-of-the-art control of growth of superlattices and quantum wells 102
- Laser processing**
- hydride — VPE embedding of InAlGaAs laser structures with SI InP:Fe 59
 - luminescence properties of p-type thin CdS films prepared by laser ablation 117
- Lead iodide clusters**
- Raman scattering in PbI_2 clusters incorporated into zeolite cages 410

- Light emitting diodes**
 barrier-modulated GaAs/InGaAs quantum well optoelectronic switch (QWOES) prepared by molecular beam epitaxy 29
 disordered superlattices 278
- Lithography**
 can nanolithography ever be a manufacturing technology? 188
- LIGA**
 collective fabrication of microsystems compatible with CMOS through the CMP service 219
- Localization**
 quantum-size layered PbS/C structures deposited by pulsed laser evaporation in vacuum 120
- Luminescence of p-type CdS**
 luminescence properties of p-type thin CdS films prepared by laser ablation 117
- Magnetic field effect**
 edge states in strong electric and magnetic fields in a two-dimensional semiconductor system 341
 excitation spectra of two-dimensional bounded electronic systems in a strong magnetic field 429
 influence of strong magnetic fields on the ionization of the modulation-doped donors in $\text{Al}_x\text{Ga}_{1-x}\text{As}-\text{GaAs}-\text{Al}_y\text{Ga}_{1-y}\text{As}$ single quantum wells 334
- MBE**
 the effects of In segregation on the emission properties of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum wells 129
- Measurement of Fermi energy**
 measurements of interface potentials in quantum wells 299
- Metalo-organic chemical vapor deposition (MOCVD)**
 high power aluminium-free InGaAsP/GaAs pumping diode lasers 34
 MBE and MOCVD growth of AlGaAs-AlAs-GaAs double barrier multiple quantum well infrared detector 176
 novel high temperature metal organic chemical vapor deposition vertical rotating-disk reactor with multizone heating for GaN and related materials 97
 self-organized InGaAs quantum disk lasers 7
- Metal-organic source modulation epitaxy**
 growth of GaAs-InP heteromaterials and corresponding strain determination 133
- Metal-organic vapour phase, epitaxy**
 enhancement of side wall growth rate during MOVPE growth on patterned substrates with CCl_4 214
- Metal-semiconductor structures**
 the control and modification of metal-semiconductor interfaces using multi quantum barriers 145
- MESFET**
 photoreflectance investigations of semiconductor device structures 267
- Microwave oscillator**
 modulation characteristics of AlAs/GaAs double barrier quantum well resonant tunneling structure at microwave frequencies 446
- Molecular beam epitaxy**
 a closed UHV focused ion beam patterning and MBE regrowth technique 208
 a hole facet wire formed by MBE regrowth over an ex-situ patterned GaAs substrate 203
 a hole facet wire formed by MBE regrowth over an ex-situ patterned GaAs substrate vii
 barrier-modulated GaAs/InGaAs quantum well optoelectronic switch (QWOES) prepared by molecular beam epitaxy 29
 formation of AlGaAs quantum wires on vicinal GaAs(110) surfaces misoriented 3° toward (111)A by molecular beam epitaxy 295
 Ge composition dependence of photoluminescence properties of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ disordered superlattices 479
 growth and characterization of strain-compensated InAsP/GaInP and InGaAs/GaInP multiple quantum wells 166
 MBE and MOCVD growth of AlGaAs-AlAs-GaAs double barrier multiple quantum well infrared detector 176
 migration of silicon atoms in planar-doped GaAs/AlGaAs modulation doped fluid effect transistor heterostructures grown by molecular beam epitaxy 149
 optical and structural characterizations for optimized growth of $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ on InP substrates by molecular beam epitaxy 109
 photoluminescence in degenerate p-type GaAs layers grown by molecular beam epitaxy 449
- Monte Carlo models**
 electron mobility in low temperature grown gallium arsenide 330
 vertical electron transport in semiconductor superlattices Monte Carlo simulation 417
- MOCVD**
 critical layer thickness in MOCVD grown InGaAs-GaAs strained quantum wells 184
 photoluminescence properties of AlGaP superlattices 454
 state-of-the-art control of growth of superlattices and quantum wells 102
- Multiple quantum wells**
 IV-VI compositional MQWs and SLs for optoelectronic applications 76
- Multi-project wafer**
 collective fabrication of microsystems compatible with CMOS through the CMP service 219
- n-i-p-i structure**
 saturation of the non-linear absorption in n-i-p-i multiple quantum well structures 72
- Nanolithography**
 can nanolithography ever be a manufacturing technology? 188
- Nitrides**
 InN thin-film growth using an ECR plasma source 171
- Non-linear effects**
 quantum transport and non-linear dynamics of interacting quantized fields and applications to nanoelectronics and optoelectronics 51
- Optical matrix element**
 anisotropic optical matrix elements in $[h\bar{h}k]$ -oriented quantum wires 288
- Optical properties**
 disordered superlattices 278
 formation of AlGaAs quantum wires on vicinal GaAs(110) surfaces misoriented 3° toward (111)A by molecular beam epitaxy 295
 influence of surface structure on surface segregation and alloy properties in (100)- and (311)-oriented InGaAs/GaAs heterostructures 318
 nanocrystalline Si: a material constructed by Si quantum dots 467
 reactive ion etched quantum wire structures for laser applications 47
 temperature dependence of luminescence in ZnSe 68
 the electronic structure and luminescence properties of porous silicon and silicon nanoclusters 459

- thermalization effects of low dimensional excitons in quantum wires and quantum wells 284
- Optical spectra in an electrical field quantum-size layered PbS/C structures deposited by pulsed laser evaporation in vacuum 120
- Optoelectronics IV-VI compositional MQWs and SLs for optoelectronic applications 76
- p-i-n diodes photoluminescence of piezoelectric strained InGaAs-GaAs multi-quantum well p-i-n structures 42
- p-n junction a hole facet wire formed by MBE regrowth over an ex-situ patterned GaAs substrate 203
- p-type CdS luminescence properties of p-type thin CdS films prepared by laser ablation 117
- Photo-CVD photo-enhanced chemical vapour deposition of hydrogenated amorphous silicon carbon using an internal discharge lamp 138
- Photoelectrochemical cells zinc doped polycrystalline CdSe films for solar energy conversion 493
- Photogenerated carriers modulation characteristics of AlAs/GaAs double barrier quantum well resonant tunneling structure at microwave frequencies 446
- Photoluminescence blue shifts from doubly δ -doped heterostructures 345 comparative studies of photoluminescence from n and p δ doping wells in GaAs 396 direct optical analysis of the carrier diffusion in semiconductor wire structures 273 fermi-edge singularity of two dimensional electrons in asymmetric coupled double quantum wells 325 field dependent vertical-transport studies in $\text{Al}_{0.24}\text{Ga}_{0.76}\text{As}/\text{GaAs}$ double-quantum-well structures 245 Ge composition dependence of photoluminescence properties of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ disordered superlattices 479 growth and characterization of strain-compensated InAsP/GaInP and InGaAs/GaInP multiple quantum wells 166 investigation of the photoluminescence linewidth broadening in symmetric and asymmetric InGaAs/GaAs n-type δ -doped quantum wells 401 native defects in gallium arsenide grown by molecular beam epitaxy and metallorganic chemical vapour deposition: effects of irradiation 160 optical and structural characterizations for optimized growth of $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ on InP substrates by molecular beam epitaxy 109 photoluminescence in degenerate p-type GaAs layers grown by molecular beam epitaxy 449 photoluminescence properties of AlAs/GaAs disordered superlattices with fixed GaAs or AlAs layer thickness 406 photoluminescence properties of AlGaP superlattices 454 temperature dependence of luminescence in ZnSe 68 visible vertical cavity surface emitting lasers at $\lambda < 650 \text{ nm}$ 12
- Photoreflectance photoreflectance investigations of semiconductor device structures 267
- Piezoelectric photoluminescence of piezoelectric strained InGaAs-GaAs multi-quantum well p-i-n structures 42
- Plasma processing InN thin-film growth using an ECR plasma source 171
- Proton irradiation native defects in gallium arsenide grown by molecular beam epitaxy and metallorganic chemical vapour deposition: effects of irradiation 160
- Quantum effects disordered superlattices 278 dual-branch electron waveguide couplers 90 formation of AlGaAs quantum wires on vicinal GaAs(110) surfaces misoriented 3° toward (111)A by molecular beam epitaxy 295 nanocrystalline Si: a material constructed by Si quantum dots 467 photoluminescence properties of AlGaP superlattices 454 quantum interference effect in GaAs/AlGaAs double quantum wells 372 quantum transport and non-linear dynamics of interacting quantized fields and applications to nanoelectronics and optoelectronics 51 theory of novel nonlinear quantum transport effects in resonant tunneling structures 303
- Quantum structures MBE and MOCVD growth of AlGaAs-AlAs-GaAs double barrier multiple quantum well infrared detector 176 nanocrystalline Si: a material constructed by Si quantum dots 467 reactive ion etched quantum wire structures for laser applications 47 self-organized InGaAs quantum disk lasers 7 single heterojunction structures for acoustic charge transfer devices 80 theoretical study of resonant tunneling in symmetrical rectangular triple-barrier structures with deep wells 421 thermalization effects of low dimensional excitons in quantum wires and quantum wells 284
- Quantum well critical layer thickness in MOCVD grown InGaAs-GaAs strained quantum wells 184 doping dependence of intersubband transitions in $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ multiple quantum wells 463 dual-branch electron waveguide couplers 90 growth and characterization of strain-compensated InAsP/GaInP and InGaAs/GaInP multiple quantum wells 166 influence of strain relaxation on the electronic properties of buried quantum wells and wires 357 investigation of the photoluminescence linewidth broadening in symmetric and asymmetric InGaAs/GaAs n-type δ -doped quantum wells 401 magnetotunnelling transport phenomena and quantum chaos in semiconductor heterostructures 239 measurements of interface potentials in quantum wells 299 new hole negative differential resistance strained-layer device 87 optimized design parameters of InGaAs-InP quantum well lasers 17 saturation of the non-linear absorption in n-i-p-i multiple quantum well structures 72 state-of-the-art control of growth of superlattices and quantum wells 102 the effects of In segregation on the emission properties of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum wells 129

- theory of novel nonlinear quantum transport effects in resonant tunneling structures 303
- the study of GaAs/InGaAs δ -doping resonant interband tunneling diode 259
- Quantum well effects**
- top sawtooth grating for GaAs/AlGaAs quantum well IR detectors 56
- Quantum wells**
- barrier-modulated GaAs/InGaAs quantum well optoelectronic switch (QWOES) prepared by molecular beam epitaxy 29
 - direct optical analysis of the carrier diffusion in semiconductor wire structures 273
 - noise characteristics of electro-absorptive logic device utilizing asymmetric Fabry-Perot etalon structure in high optical power 64
 - quantum interference effect in GaAs/AlGaAs double quantum wells 372
 - switching characteristics of nonbiased optical bistability in asymmetric Fabry-Perot S-SEEDs made of extremely shallow quantum well structures 24
- Quantum wires**
- anisotropic optical matrix elements in $[hhk]$ -oriented quantum wires 288
 - a novel approach in fabrication and study of laterally quantum-confined resonant tunnelling diodes 192
- Raman scattering**
- optical and structural characterizations for optimized growth of $In_{0.52}Al_{0.48}As$ on InP substrates by molecular beam epitaxy 109
 - Raman scattering in PbI_2 clusters incorporated into zeolite cages 410
- Real-time optical process monitoring**
- real-time monitoring of heteroepitaxial growth processes on the silicon(001) surface by p-polarized reflectance spectroscopy 472
- Re number**
- analysis of reaction gases flow in CVD processes 156
- Resonant enhancement**
- the influence of exciton migration on photoluminescence lifetime in growth-interrupted GaAs/AlAs single quantum wells 125
- Resonant interband tunnelling**
- investigation of resonant interband tunneling structures using a three-band $\vec{k} \cdot \vec{p}$ model 435
- Resonant tunnelling**
- a novel approach in fabrication and study of laterally quantum-confined resonant tunnelling diodes 192
 - modulation characteristics of AlAs/GaAs double barrier quantum well resonant tunneling structure at microwave frequencies 446
 - theoretical study of resonant tunneling in symmetrical rectangular triple-barrier structures with deep wells 421
- Resonant tunnelling diodes**
- side-gated GaAs/AlGaAs double barrier resonant tunnelling diodes formed by patterned substrate regrowth 198
- Resonant tunnelling structures**
- theory of novel nonlinear quantum transport effects in resonant tunneling structures 303
- Schottky barrier**
- the control and modification of metal-semiconductor interfaces using multi quantum barriers 145
- Self electro-optic effect device**
- switching characteristics of nonbiased optical bistability in asymmetric Fabry-Perot S-SEEDs made of extremely shallow quantum well structures 24
- Scanning tunnelling microscopy**
- Be delta-doped layers in GaAs studied by scanning tunnelling microscopy 485
- Schottky barrier**
- ballistic electron emission microscopy of InAs/ $Ga_{1-x}Al_xAs$ relaxed heterostructure interfaces 349
- Segregation**
- influence of surface structure on surface segregation and alloy properties in (100)- and (311)-oriented InGaAs/GaAs heterostructures 318
 - the effects of In segregation on the emission properties of $In_xGa_{1-x}As/GaAs$ quantum wells 129
- Self electro-optic effect device**
- noise characteristics of electro-absorptive logic device utilizing asymmetric Fabry-Perot etalon structure in high optical power 64
- Semiconductor devices**
- are quantum semiconductor devices delivering? 1
 - characterization of Ni/Ge/Au/Ni/Au contact metallization on AlGaAs/InGaAs heterostructures for pseudomorphic heterojunction field effect transistor application 234
 - dual-branch electron waveguide couplers 90
 - examination of internally delta-doped gallium arsenide resonant tunnelling structures 353
 - quantum transport and non-linear dynamics of interacting quantized fields and applications to nanoelectronics and optoelectronics 51
 - reactive ion etched quantum wire structures for laser applications 47
 - selective wet etching of a GaAs/ $Al_xGa_{1-x}As$ heterostructure with citric acid-hydrogen peroxide solutions for pseudomorphic GaAs/ $Al_xGa_{1-x}As$ heterofunction field effect transistor fabrication 230
 - self-organized InGaAs quantum disk lasers 7
- Semiconductor for devices**
- proton implantation of $Al_xGa_{1-x}As/GaAs$ resonant-tunnelling diode structures 376
- Semiconductors**
- direct optical analysis of the carrier diffusion in semiconductor wire structures 273
 - edge states in strong electric and magnetic fields in a two-dimensional semiconductor system 341
 - magnetotunnelling transport phenomena and quantum chaos in semiconductor heterostructures 239
 - photoluminescence of piezoelectric strained InGaAs-GaAs multi-quantum well p-i-n structures 42
 - spontaneous anisotropic chemical etching as a nanostructure surface modification method for the A^{III}B^V semiconductors 224
 - temperature dependence of luminescence in ZnSe 68
 - zinc doped polycrystalline CdSe films for solar energy conversion 493
- Shape effects**
- shape effects of the conductance of a quantum ballistic constriction in a two-dimensional electron gas 440
- Shubnikov-de Haas**
- anomalous peaks in the Shubnikov-de Haas spectra of a top gated AlGaAs/GaAs heterostructure 382
- SiGe**
- Ge composition dependence of photoluminescence properties of $Si_{1-x}Ge_x/Si$ disordered superlattices 479

- Silicon**
- nanocrystalline Si: a material constructed by Si quantum dots 467
 - photo-enhanced chemical vapour deposition of hydrogenated amorphous silicon carbon using an internal discharge lamp 138
 - the electronic structure and luminescence properties of porous silicon and silicon nanoclusters 459
- Silicon grating**
- top sawtooth grating for GaAs/AlGaAs quantum well IR detectors 56
- Single quantum wells**
- role of the InAs monomolecular plane inserted in bulk GaAs 386
- SiN films**
- analysis of reaction gases flow in CVD processes 156
- Si substrate**
- analysis of reaction gases flow in CVD processes 156
- Strain relaxation**
- influence of strain relaxation on the electronic properties of buried quantum wells and wires 357
- Sublimation method**
- temperature dependence of luminescence in ZnSe 68
- Superlattices**
- are quantum semiconductor devices delivering? 1
 - atomic-scale characterization of interfaces in the GaAs/AlGaAs superlattices 180
 - disordered superlattices 278
 - Ge composition dependence of photoluminescence properties of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ disordered superlattices 479
 - IV-VI compositional MQWs and SLs for optoelectronic applications 76
 - non-linear generation of alternating current harmonics in quantum dot superlattice miniband transport 256
 - photo-Hall studies of modulation-doped field-effect transistor heterostructures using $(\text{InAs})_m(\text{GaAs})_n$ superlattice channels 391
 - photoluminescence properties of AlGaP superlattices 454
 - photoluminescence properties of AlAs/GaAs disordered superlattices with fixed GaAs or AlAs layer thickness 406
 - the control and modification of metal-semiconductor interfaces using multi quantum barriers 145
 - theoretical study of resonant tunneling in symmetrical rectangular triple-barrier structures with deep wells 421
 - vertical electron transport in semiconductor superlattices Monte Carlo simulation 417
- Surface acoustic waves**
- single heterojunction structures for acoustic charge transfer devices 80
- Surface and interface states**
- hydride — VPE embedding of InAlGaAs laser structures with SI InP:Fe 59
- Surface micromachining**
- collective fabrication of microsystems compatible with CMOS through the CMP service 219
- Surface morphology**
- influence of surface structure on surface segregation and alloy properties in (100)- and (311)-oriented InGaAs/GaAs heterostructures 318
- Surface structure**
- a comparison of observed and simulated scanning tunneling images of the reconstructed GaAs(001) surface 489
- Switching time**
- switching characteristics of nonbiased optical bistability in asymmetric Fabry-Perot S-SEEDs made of extremely shallow quantum well structures 24
- Theory of electron transport**
- quantum transport and non-linear dynamics of interacting quantized fields and applications to nanoelectronics and optoelectronics 51
 - theory of novel nonlinear quantum transport effects in resonant tunneling structures 303
- Thin films**
- critical layer thickness in MOCVD grown InGaAs-GaAs strained quantum wells 184
 - InN thin-film growth using an ECR plasma source 171
 - luminescence properties of p-type thin CdS films prepared by laser ablation 117
- Tunnelling**
- investigation of resonant interband tunneling structures using a three-band $\vec{k} \cdot \vec{p}$ model 435
 - magnetotunnelling transport phenomena and quantum chaos in semiconductor heterostructures 239
 - new hole negative differential resistance strained-layer device 87
 - proton implantation of $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ resonant-tunnelling diode structures 376
 - the study of GaAs/InGaAs δ -doping resonant interband tunneling diode 259
- Two-dimensional electron gas**
- a closed UHV focused ion beam patterning and MBE regrowth technique 208
- Vacancy**
- temperature dependence of luminescence in ZnSe 68
- Vapour phase epitaxy**
- hydride — VPE embedding of InAlGaAs laser structures with SI InP:Fe 59
- VCSEL**
- state-of-the-art control of growth of superlattices and quantum wells 102
- VCSELs**
- visible vertical cavity surface emitting lasers at $\lambda < 650$ nm 12
- Visible lasers**
- visible vertical cavity surface emitting lasers at $\lambda < 650$ nm 12
- Vorticity**
- analysis of reaction gases flow in CVD processes 156
- X-ray diffraction**
- optical and structural characterizations for optimized growth of $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ on InP substrates by molecular beam epitaxy 109
- Zeolites**
- raman scattering in PbI_2 clusters incorporated into zeolite cages 410
- ZnSe**
- temperature dependence of luminescence in ZnSe 68

